

ELECTRICAL SPECIFICATIONS

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VOLTAGE R	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$					
	04	400	500						
	08	800	900						
VS-ST300S	12	1200	1300	50					
V3-313003	16	1600	1700	50					
	18		1900						
	20	2000	2100						

PRIMARY CHARACTERISTICS

I _{T(AV)}	300 A				
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1600 V, 1800 V, 2000 V				
V _{TM}	1.28 V				
I _{GT}	200 mA				
TJ	-40 °C to +125 °C				
Package	TO-118 (TO-209AE)				
Circuit configuration	Single SCR				

TO-118 (TO- 209AE)

FEATURES

Phase Control Thyristors (Stud Version), 300 A

- Center amplifying gate
- International standard case TO-118 (TO-209AE)
- Hermetic metal case with ceramic insulator
- Threaded studs UNF 3/4"-16UNF-2A or ISO M24 x 1.5
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
I		300	А				
I _{T(AV)}	T _C	75	°C				
I _{T(RMS)}		470					
less s	50 Hz	8000	A				
ITSM	60 Hz	8380					
l ² t	50 Hz	320	kA ² s				
1-1	60 Hz	292	KA-5				
V _{DRM} /V _{RRM}		400 to 2000	V				
t _q	Typical	100	μs				

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 1
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VS-ST300SPbF Series

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RoHS

COMPLIANT

°C

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ABSOLUTE MAXIMUM RATING	S					
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS
Maximum average on-state current	1	180° condu	300	А		
at case temperature	I _{T(AV)}				75	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 64 °C	case temperat	ure	470	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle	1	t = 8.3 ms	reapplied	Sinusoidal half wave, initial T _J = T _J maximum	8380	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		6730	
		t = 8.3 ms	reapplied		7040	
		t = 10 ms	No voltage reapplied		320	
	l ² t	t = 8.3 ms			292	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		226	
		t = 8.3 ms	reapplied		207	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			3200	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T _J = T _J maximum			0.97	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	0.98	v		
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.74	mΩ
High level value of on-state slope resistance rt2		$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.73	1115.2
Maximum on-state voltage	V _{TM}	I_{pk} = 940 A, T_J = T_J maximum, t_p = 10 ms sine pulse			1.66	V
Maximum holding current	Ι _Η	T _ 05 °C	anada aunahi 1	2. V registive load	600	mA
Typical latching current	١L	$1_{\rm J} = 25$ C,	$T_J = 25 \text{ °C}$, anode supply 12 V resistive load			mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs				
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0					
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs				

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	30	mA			



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TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	
PANAMETER	STMBOL				MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	10	0.0	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$	3	.0	Α
Maximum peak positive gate voltage +			t < 5 mg	20		v
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			5.0	
		T _J = -40 °C		200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	mA
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-	
		T _J = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	12 v anoue to cathode applied	1.8	3	V
		T _J = 125 °C		1.1	-	
DC gate current not to trigger	I _{GD}	T T. movimum	Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to 125	O		
Maximum storage temperature range	T _{Stg}		-40 to 150			
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.10	к/w		
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.03	r\/ vv		
Mounting torque, ± 10 %		Non-lubricated threads	48.5 (425)	N · m (lbf · in)		
Approximate weight			535	g		
Case style		See dimensions - link at the end of datasheet	TO-118 (TO-	209AE)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS					
180°	0.011	0.008							
120°	0.013	0.014							
90°	0.017	0.018	$T_J = T_J$ maximum	K/W					
60°	0.025	0.026							
30°	0.041	0.042							

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

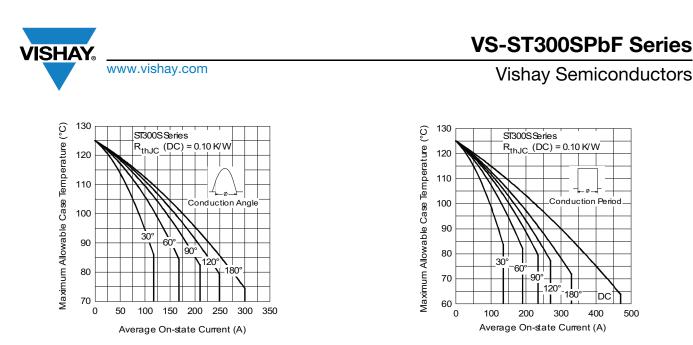


Fig. 1 - Current Ratings Characteristics

Fig. 2 - Current Ratings Characteristics

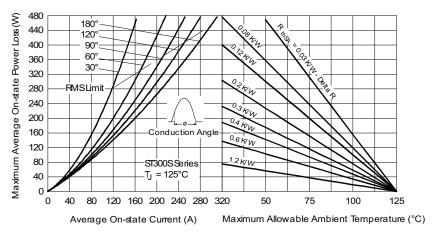


Fig. 3 - On-State Power Loss Characteristics

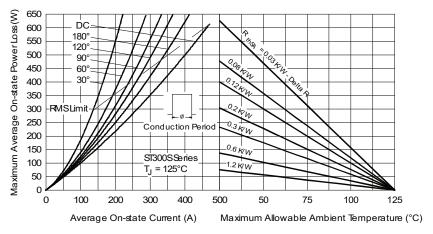


Fig. 4 - On-State Power Loss Characteristics

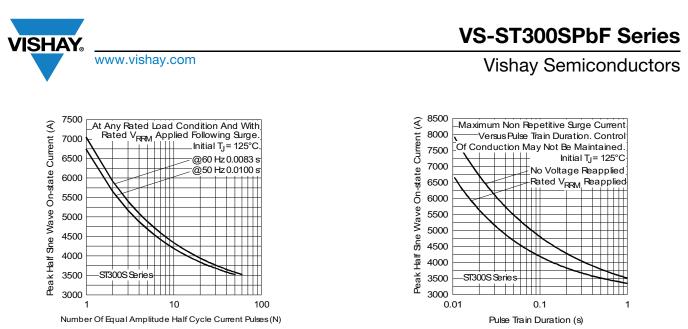


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

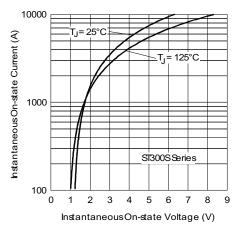


Fig. 7 - On-State Voltage Drop Characteristics

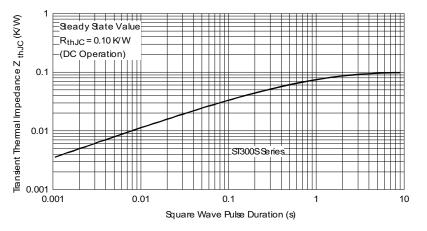


Fig. 8 - Thermal Impedance ZthJC Characteristics

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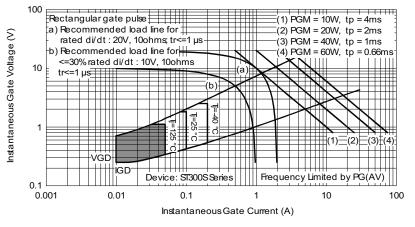


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	ST	30	0	S	20	Р	0	-	PbF
L	1	2	3	4	5	6	7	8	9	10
[1 - 2 -		nay Sen ristor	niconduc	ctors pro	oduct				
	3 -	-		art numt	ber					
	4 -		-	ter grade						
[5 -	S =	Compre	ession b	onding s	stud				
	6 -	Volt	age coo	de x 100	= V _{RRM}	(see V	oltage F	Ratings	table)	
l	7 -				16UNF-					
-	_	M =	stud ba	ase metr	ic thread	ds (M24	x 1.5)			
l	8 -	0 =	Eyelet t	erminals	s (gate a	ind auxi	liary ca	thode le	eads)	
		1 =	Fast-on	termina	ls (gate	and au	xiliary c	athode	leads)	
		3 =	Threade	ed top te	erminal 3	3/8" 24L	JNF-2A			
[9 -	Crit	ical dV/	dt: • No	ne = 50	0 V/µs (standar	d value)	
-				• L =	1000 V	′/µs (spe	ecial sel	ection)		
l	10 -	Nor	ne = Sta	ndard p	roductio	n				
	-	PbF	= Lead	l (Pb)-fre	ее					

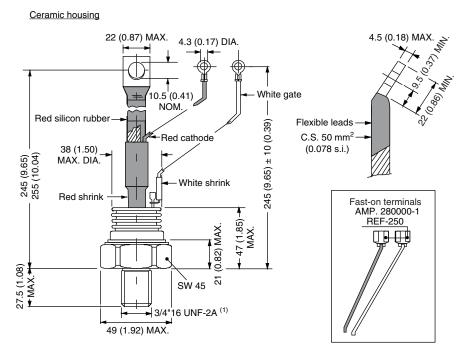
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95084			



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TO-209AE (TO-118)

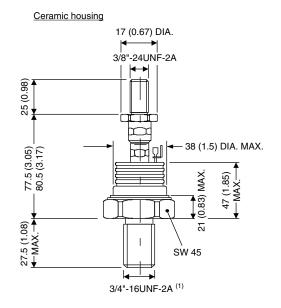
DIMENSIONS - TO-209AE (TO-118) in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length screw 21 (0.83) maximum

DIMENSIONS - TO-209AE (TO-118) WITH TOP THREAD TERMINAL 3/8" in millimeters (inches)



Note

⁽¹⁾ For metric device: M24 x 1.5 - length screw 21 (0.83) maximum



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